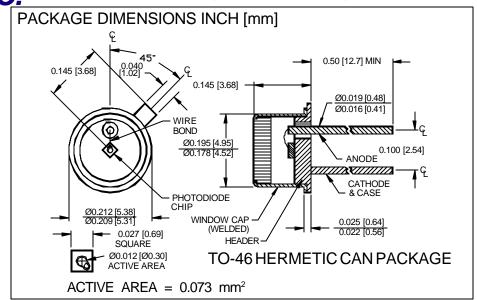
PHOTONIC Silicon Photodiode, Blue Enhanced Photoconductive DETECTORS INC. (MRD 510) Industry Equivalent Type PDB-C120





FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

DESCRIPTION

The **PDB-C120** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-46 metal can with a flat window.

APPLICATIONS

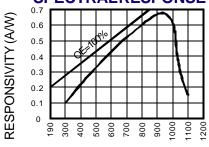
- Fiber optic
- Laser detection
- Light demodulation
- Matched to I.R. LEDs

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		200	V
T _{STG}	Storage Temperature	-65	+150	∘C
T _o	Operating Temperature Range	-55	+125	⊙C
T _s	Soldering Temperature*		+240	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRALRESPONSE



WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l _{sc}	Short Circuit Current	H = 100 fc, 2850 K	1.2	1.5		μΑ
I _D	Dark Current	$H = 0, V_R = 10 V$		0.5	2.0	nA
R _{sH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$	400	500		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C _J	Junction Capacitance	$H = 0, V_R = 10 V^{**}$		1		pF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	Ι = 10 μΑ	100	150		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		9.0x10 ⁻¹⁵		W/ √ Hz
tr	Response Time	$RL = 1 K\Omega V_R = 50 V$		1.0		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f=1 MHz [FORM NO. 100-PDB-C120 REV B]